

FERROELECTRIC MEMORY DEVICE AND METHOD OF FORMING THE SAME

ABSTRACT OF THE DISCLOSURE

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A ferroelectric memory device along with a method of forming the same are provided. A first interlayer insulating layer is formed on a semiconductor substrate. A buried contact structure is formed on the first interlayer insulating layer. The buried contact structure is electrically connected to the substrate through a first contact hole extending through the first
10 interlayer insulating layer. A blocking layer covers or encapsulates the buried contact structure and the first interlayer insulating layer. A second interlayer insulating layer is formed on the blocking layer. A ferroelectric capacitor formed on the second interlayer insulating layer and is electrically connected to the buried contact structure through a second contact hole that penetrates the second interlayer insulating layer and the blocking layer.

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